

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFB4110G, IIRFB4110G

• FEATURES

- Static drain-source on-resistance: RDs(on) ≤4.5mΩ
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

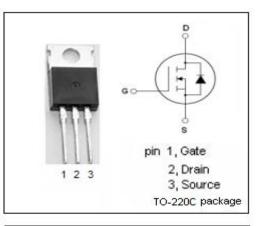
· reliable device for use in a wide variety of applications

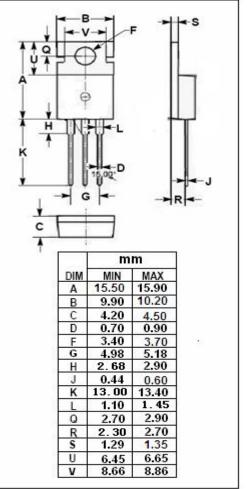
• ABSOLUTE MAXIMUM RATINGS(Ta=25 C)							
SYMBOL	PARAMETER	VALUE	UNIT				
VDSS	Drain-Source Voltage	100	V				
V _{GS}	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous	180	А				
I _{DM}	Drain Current-Single Pulsed	670	A				
PD	Total Dissipation @T _c =25°C	@T _c =25°C 370					
Tj	Max. Operating Junction Temperature 175		°C				
T _{stg}	Storage Temperature	-55~175	°C				

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.402	°C/W
Rth(ch-a)	th(ch-a) Channel-to-ambient thermal resistance		°C/W





isc website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =75A			4.5	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V; V _{GS} = 0V			20	μ Α
V _{SD}	Diode forward voltage	Is=75A, V _{GS} = 0V			1.3	V

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